Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	99	("5319395" "5877742" "5764581" "6072185" "6237122" "6243348" "4796260" "5430861" "5805155" "5845292" "5930518" "6181609" "4313160" "4455483" "4847842" "5255383" "5321699" "5386422" "5388074" "5469444" "5481531" "5524234" "5524235" "5608892" "5684774" "5797027" "5841717" "5860111" "5917429" "6163832" "6178121" "6233668" "4849974" "4849976" "4855903" "4953121" "5274782" "5280584" "5416916" "5469551" "5477492" "5511212" "5537577" "5561671" "5657398" "5664149" "5742509" "5781495" "5809273" "5818789").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 11:00
1.2	50	("5319395" "5877742" "5764581" "6072185" "6237122" "6243348" "4796260" "5430861" "5805155" "5845292" "5930518" "6181609" "4313160" "4455483" "4847842" "5255383" "5321699" "5386422" "5388074" "5469444" "5481531" "5524234" "5524235" "5608892" "5684774" "5797027" "5841717" "5860111" "5917429" "6163832" "6178121" "6233668" "4849974" "4849976" "4855903" "4953121" "5274782" "5280584" "5416916" "5469551" "5477492" "5511212" "5537577" "5561671" "5657398" "5664149" "5742509" "5781495" "5809273" "5818789").pn.	USPAT	OR	ON	2006/02/20 11:05
L3	3977	(write and read) same (time adj period)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 11:07
L4	4	13 and 12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 11:06
L5	1089	(write and read) same (time adj period) same (first)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 11:07

L6	638	(write and read) same (time adj period) same (first and second)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 11:07
L7	8	l6 and (data near2 retention)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 12:11
L8	2913	memory with (data near2 retention)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 12:12
L9	594	(memory with (data near2 retention)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 12:12
L10	536260	(test testing tester tested and (memory with (data near2 retention))).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 12:12
L11	63	((test testing tester tested) and (memory with (data near2 retention))).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 12:12
L12	8	("5034923" "5255230" "5361232" "5428574" "5491665" "5733032" "5936902" "6378102").PN. OR ("6681350"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 15:38
L13	15	("3655959" "4093958" "5132772" "5222066" "5241266" "5361232" "5519333" "5570317" "5654588" "5949242" "6067262" "6167541" "6175244" "6208567").PN. OR ("6697978").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 15:44
L14	3	l13 and (data near2 retention)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 17:33

L15	55	("3795859" "4541090" "4594711" "4601034" "4635261" "4801870" "4872168" "4903266" "4910735" "5033048").PN. OR ("5222066"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:32
L16	5	l15 and (data near2 retention)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 18:18
L17	18	("5222066" "5491665" "5495448" "5559745" "5577050" "5642318").PN. OR ("5835429"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 18:17
L18	9	I17 and (data near2 retention)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 18:35
L19	4	"611099"	US-PGPUB; USPAT	OR	ON	2006/02/20 18:36
L20	5	"614642"	US-PGPUB; USPAT	OR	ON	2006/02/20 21:38
L21	7	"6496947"	USPAT	OR	ON	2006/02/20 21:38





☐ Search Result - Print Format

< Back to Previous Page

Key: IEEE JNL = IEEE Journal or Magazine, IEE JNL = IEE Journal or Magazine, IEEE CNF = IEEE Conference, IEEE CNF = IEEE Standard

1. Mobile ion-induced data retention failure in NOR flash memory cell

Lee, W.H.; Dong-Kyu Lee; Keon-Soo Kim; Kun-Ok Ahn; Kang-Deog Suh; Device and Materials Reliability, IEEE Transactions on Volume 1, Issue 2, June 2001 Page(s):128 - 132
IEEE JNL

2. Enhanced quality of tunnel oxide by in-situ screen oxide for embedded flash memory application

Nakamura, T.; Ichii, M.;

Semiconductor Manufacturing, 2000. Proceedings of ISSM 2000. The Ninth International Symposium on 26-28 Sept. 2000 Page(s):430 - 433

IEEE CNF

The effect of the floating gate/tunnel SiO₂ interface on FLASH memory data retention reliability

Kubota, T.; Ando, K.; Muramatsu, S.; Reliability Physics Symposium, 1996. 34th Annual Proceedings., IEEE International 30 April-2 May 1996 Page(s):12 - 16

IEEE CNF

4. Block-based multiperiod dynamic memory design for low data-retention power

Joohee Kim; Papaefthymiou, M.C.;

Very Large Scale Integration (VLSI) Systems, IEEE Transactions on

Volume 11, Issue 6, Dec. 2003 Page(s):1006 - 1018

IEEE JNL

Effects of Fowler Nordheim tunneling stress vs. Channel Hot Electron stress on data retention characteristics of floating gate non-volatile memories

Suhail, M.; Harp, T.; Bridwell, J.; Kuhn, P.J.; Reliability Physics Symposium Proceedings, 2002. 40th Annual 7-11 April 2002 Page(s):439 - 440

IEEE CNF

6. The mechanical stress effects on data retention reliability of NOR flash memory

Park, Y.M.; Lee, J.S.; Kim, M.; Choi, M.K.; Kim, K.; Han, J.I.; Kwon, D.W.; Lee, W.K.; Song, Y.H.; Suh, K.D.; Electron Devices Meeting, 2001. IEDM Technical Digest. International 2-5 Dec. 2001 Page(s):32.4.1 - 32.4.4

IEEE CNF

7. Data retention characteristics of sub-100 nm NAND flash memory cells

Jae-Duk Lee; Jeong-Hyuk Choi; Donggun Park; Kinam Kim; Electron Device Letters, IEEE Volume 24, Issue 12, Dec. 2003 Page(s):748 - 750 IEEE JNL

B. Study of data retention for nanocrystal Flash memories

Compagnoni, C.M.; Ielmini, D.; Spinelli, A.S.; Lacaita, A.L.; Previtali, C.; Gerardi, C.; Reliability Physics Symposium Proceedings, 2003. 41st Annual. 2003 IEEE International 30 March-4 April 2003 Page(s):506 - 512

IEEE CNF

A forced-voltage technique to test data retention faults in CMOS SRAM by IDDO testing

Castillejos, J.; Champac, V.H.;

Circuits and Systems, 1997. Proceedings of the 40th Midwest Symposium on

Volume 1, 3-6 Aug. 1997 Page(s):433 - 436 vol.1 IEEE CNF

10. A new extrapolation law for data-retention time-to-failure of nonvolatile memories

De Salvo, B.; Ghibaudo, G.; Pananakakis, G.; Guillaumot, B.; Candelier, P.; Reimbold, G.; Electron Device Letters, IEEE Volume 20, Issue 5, May 1999 Page(s):197 - 199

IEEE JNL

11. Low-voltage DRAM sensing scheme with offset-cancellation sense amplifier

Sanghoon Hong; Sejun Kim; Jae-Kyung Wee; Seongsoo Lee; Solid-State Circuits, IEEE Journal of Volume 37, Issue 10, Oct. 2002 Page(s):1356 - 1360 IEEE JNL

12. Cause of data retention loss in a nitride-based localized trapping storage flash memory cell

Tsai, W.J.; Gu, S.H.; Zous, N.K.; Yeh, C.C.; Liu, C.C.; Chen, C.H.; Tahui Wang; Pan, S.; Chih-Yuan Lu; Reliability Physics Symposium Proceedings, 2002. 40th Annual 7-11 April 2002 Page(s):34 - 38

IEEE CNF

13. Data retention failure in NOR flash memory cells

Lee, W.H.; Dong-Kyu Lee; Young-Min Park; Keon-Soo Kim; Kun-Ok Ahn; Kang-Deog Suh; Reliability Physics Symposium, 2001. Proceedings. 39th Annual. 2001 IEEE International 30 April-3 May 2001 Page(s):57 - 60

IEEE CNF

14. A new data retention mechanism after endurance stress on flash memory

Kameyama, H.; Okuyama, Y.; Kamohara, S.; Kubota, K.; Kume, H.; Okuyama, K.; Manabe, Y.; Nozoe, A.; Uchida, H.; Hidaka, M.; Ogura, K.; Reliability Physics Symposium, 2000. Proceedings. 38th Annual 2000 IEEE International 10-13 April 2000 Page(s):194 - 199

IEEE CNF

15. A novel MONOS nonvolatile memory device ensuring 10-year data retention after 10⁷ erase/write cycles

Minami, S.-i.; Kamigaki, Y.;

Electron Devices, IEEE Transactions on

Volume 40, Issue 11, Nov 1993 Page(s):2011 - 2017

IEEE JNL

16. Experimental and theoretical investigation of nonvolatile memory data-retention

De Salvo, B.; Ghibaudo, G.; Pananakakis, G.; Reimbold, G.; Mondond, F.; Guillaumot, B.; Candelier, P.; Electron Devices, IEEE Transactions on Volume 46, Issue 7, July 1999 Page(s):1518 - 1524

IEEE JNL

17. Memory operations of 1T2C-type ferroelectric memory cell with excellent data retention characteristics

Sung-Min Yoon; Ishiwara, H.;

Electron Devices, IEEE Transactions on

Volume 48, Issue 9, Sept. 2001 Page(s):2002 - 2008

IEEE JNL

18. Bit line sensing strategy for testing for data retention faults in CMOS SRAMs

Champac, V.H.; Avendano, V.; Linares, M.; Electronics Letters

Volume 36, Issue 14, 6 July 2000 Page(s):1182 - 1183

IEE JNL

Recent progress in FET-type ferroelectric memories

Ishiwara, H.:

Electron Devices Meeting, 2003. IEDM '03 Technical Digest. IEEE International

8-10 Dec. 2003 Page(s):10.3.1 - 10.3.4

IEEE CNF

20. Statistical simulations to inspect and predict data retention and program disturbs in flash memories

Larcher, L.; Pavan, P.;

Electron Devices Meeting, 2003. IEDM '03 Technical Digest. IEEE International

8-10 Dec. 2003 Page(s):7.3.1 - 7.3.4

IEEE CNF

21. Energy-aware memory allocation in heterogeneous non-volatile memory systems

Hyung Gyu Lee; Naehyuck Chang;

Low Power Electronics and Design, 2003. ISLPED '03. Proceedings of the 2003 International Symposium on

25-27 Aug. 2003 Page(s):420 - 423

IEEE CNF

22. Degradation of tunnel oxide by FN current stress and its effects on data retention characteristics of 90 nm NAND flash memory cells

Jae-Duk Lee; Jeong-Hyuk Choi; Donggun Park; Kinam Kim;

Reliability Physics Symposium Proceedings, 2003. 41st Annual. 2003 IEEE International

30 March-4 April 2003 Page(s):497 - 501

IEEE CNF

23. Characterization of multi-barrier tunneling diodes and vertical transistors using 2-D device simulation

Kwan-Do Kim; Keun-Ho Lee; Seung-Jae Baik; Jun-Ha Lee; Tai-Kyung Kim; Jeong-Taek Kong; Simulation of Semiconductor Processes and Devices, 2002. SISPAD 2002. International Conference on 4-6 Sept. 2002 Page(s):167 - 170

IEEE CNF

24. DRG-cache: a data retention gated-ground cache for low power

Agarwal, A.; Hai Li; Roy, K.; Design Automation Conference, 2002. Proceedings. 39th 10-14 June 2002 Page(s):473 - 478

IEEE CNF

25. Statistical modeling of the program/erase cycling acceleration of low temperature data retention in floating gate nonvolatile memories

Hoefler, A.; Higman, J.M.; Harp, T.; Kuhn, P.J.; Reliability Physics Symposium Proceedings, 2002. 40th Annual 7-11 April 2002 Page(s):21 - 25

IEEE CNF



© Copyright 2006 IEEE - All Rights Reserved





☐ Search Result - Print Format

< Back to Previous Page

Key: IEEE JNL = IEEE Journal or Magazine, IEE JNL = IEE Journal or Magazine, IEEE CNF = IEEE Conference, IEEE CNF = IEEE Standard

1. Quick address detection of anomalous memory cells in a flash memory test structure Himeno, T.; Hazama, H.; Yaegashi, T.; Sakui, K.; Kanda, K.; Itoh, Y.; Miyamoto, J.;

Semiconductor Manufacturing, IEEE Transactions on Volume 10, Issue 2, May 1997 Page(s):196 - 200

IEEE JNL

2. An efficient BIST method for testing of embedded SRAMs

Tehranipour, M.H.; Navabi, Z.; Fakhraie, S.M.; Circuits and Systems, 2001. ISCAS 2001. The 2001 IEEE International Symposium on Volume 5, 6-9 May 2001 Page(s):73 - 76 vol. 5

IEEE CNF

3. Zero-overhead BIST for internal-SRAM testing

Tehranipour, M.H.; Navabi, Z.; Microelectronics, 2000. ICM 2000. Proceedings of the 12th International Conference on 31 Oct.-2 Nov. 2000 Page(s):109 - 112

IEEE CNF

4. Assessing SRAM test coverage for sub-micron CMOS technologies

Kim, V.; Chen, T.; VLSI Test Symposium, 1997., 15th IEEE 27 April-1 May 1997 Page(s):24 - 30

IEEE CNF

5. Self-learning signature analysis for non-volatile memory testing

Olivo, P.; Dalpasso, M.; Test Conference, 1996. Proceedings., International 20-25 Oct. 1996 Page(s):303 - 308

IEEE CNF

Indexed by

© Copyright 2006 IEEE - All Rights Reserved



PALM INTRANET

Day: Monday Date: 2/20/2006 Time: 11:21:07

Inventor Name Search Result

Your Search was:

Last Name = DIXIT

First Name = CHARUTOSH

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09449324	6542834	150	11/24/1999	CAPACITANCE ESTIMATION	DIXIT, CHARUTOSH
09515250	6484297	150	02/29/2000	4K DERATING SCHEME FOR PROPAGATION DELAY AND SERUP/HOLD TIME COMPUTATION	DIXIT, CHARUTOSH
<u>09727426</u>	6449760	150	11/30/2000	PIN PLACEMENT METHOD FOR INTEGRATED CIRCUITS	DIXIT, CHARUTOSH
10163208	6829754	150	06/04/2002	METHOD AND SYSTEM FOR CHECKING FOR POWER ERRORS IN ASIC DESIGNS	DIXIT, CHARUTOSH
10614642	Not Issued	30		Method and system of testing data retention of memory	DIXIT, CHARUTOSH
60194073	Not Issued	159		Driver waveform modling using two ceffectives	DIXIT, CHARUTOSH
60450604	Not Issued	159		Managing peak and average power consumption during data retention testing of memories	DIXIT, CHARUTOSH
<u>09814417</u>	6845348	150	03/21/2001	DRIVER WAVEFORM MODELING WITH MULTIPLE EFFECTIVE CAPACITANCES	DIXIT, CHARUTOSHI

Inventor Search Completed: No Records to Display.

Search Another: Inventor Last Name First Name

CHARUTOSH Search

To go back use Back button on your browser toolbar.

Back to $\underline{PALM} \mid \underline{ASSIGNMENT} \mid \underline{OASIS} \mid Home page$



PALM INTRANET

Day: Monday Date: 2/20/2006 Time: 11:21:23

Inventor Name Search Result

Your Search was:

Last Name = SHEN

First Name = WILLIAM

Application#	Patent#	Status	Date Filed	Title	Inventor Name
10614642	Not Issued	30		Method and system of testing data retention of memory	SHEN, WILLIAM
10767314	6888367	150	01/28/2004	METHOD AND APPARATUS FOR TESTING INTEGRATED CIRCUIT CORE MODULES	SHEN, WILLIAM
10975315	Not Issued	30	10/28/2004	Test clocking scheme	SHEN, WILLIAM
60450604	Not Issued	159		Managing peak and average power consumption during data retention testing of memories	SHEN, WILLIAM
60104889	Not Issued	159	10/20/1998	ADDRESS WRAP FUNCTION FOR ADDRESSABLE SEMICONDUCTOR DEVICES	SHEN, WILLIAM S.
09796285	Not Issued	95	02/28/2001	MULTI-CYCLE SYMBOL LEVEL ERROR CORRECTION AND MEMORY SYSTEM	SHEN, WILLIAM W.
10171863	6667929	150		POWER GOVERNOR FOR DYNAMIC RAM	SHEN, WILLIAM W.
10280315	Not Issued	161		Volatilization of a drug from an inclusion complex	SHEN, WILLIAM W.
10861554	Not Issued	30	06/03/2004	Multiple dose condensation aerosol devices and methods of forming condensation aerosols	SHEN, WILLIAM W.
10996162	Not Issued	30		Treatment of breakthrough pain by drug aerosol inhalation	SHEN, WILLIAM W.
60335049	Not Issued	159		Volatilization of nicotine from an inclusion complex	SHEN, WILLIAM W.
60371457	Not Issued	159	04/09/2002	Volatilization of a drug from an inclusion complex	SHEN, WILLIAM W.
60530058	Not Issued	159	12/16/2003	Treatment of breakthrough pain by drug aerosol inhalation	SHEN, WILLIAM W.
07755209	5267242			METHOD AND APPARATUS FOR SUBSTITUTING SPARE MEMORY CHIP FOR MALFUNCTIONING MEMORY CHIP WITH SCRUBBING	SHEN, WILLIAM W.
08085215	<u>5479640</u>	250	06/30/1993	SIMPLIFIED MEMORY ROW	SHEN, WILLIAM W.

i i				REDRIVE SYSTEM	
08260125	Not Issued	166	06/15/1994	BARCODE SCANNER FOR POOR OR LOW CONTRAST SURFACES	SHEN, WILLIAM W.
08350579	<u>5581071</u>	150	12/06/1994	BARCODE SCANNER WITH ADJUSTABLE LIGHT SOURCE INTENSITY	SHEN, WILLIAM W.
08414553	Not Issued	161	03/31/1995	MECHANISM FOR LOCKING A UNIT OF STORAGE IN A MULTIPROCESSOR SYSTEM	SHEN, WILLIAM W.
08452364	Not Issued	161	05/30/1995	MECHANISM FOR LOCKING A UNIT OF STORAGE IN A MULTIPROCESSOR SYSTEM	SHEN, WILLIAM W.
08570446	<u>5691996</u>	250	12/11/1995	MEMORY IMPLEMENTED ERROR DETECTION AND CORRECTION CODE WITH ADDRESS PARITY BITS	SHEN, WILLIAM W.
08570448	5768294	150	12/11/1995	MEMORY IMPLEMENTED ERROR DETECTION AND CORRECTION CODE CAPABLE OF DETECTING ERRORS IN FETCHING DATA FROM A WRONG ADDRESS	SHEN, WILLIAM W.
08599672	Not Issued	161	02/12/1996	BARCODE SCANNER FOR POOR OR LOW CONTRAST SURFACES	SHEN, WILLIAM W.
08765988	Not Issued	161	01/10/1997	SHARED CACHE MEMORY DEVICE	SHEN, WILLIAM W.
09325814	6480982	150	06/04/1999	COMPUTER RAM MEMORY SYSTEM WITH ENHANCED SCRUBBING AND SPARING	SHEN, WILLIAM W.
09326233	6386456	150	06/04/1999	MEMORY CARD IDENTIFICATION SYSTEM	SHEN, WILLIAM W.
09855240	6941414	150	05/15/2001	HIGH SPEED EMBEDDED DRAM WITH SRAM-LIKE INTERFACE	SHEN, WILLIAM WU
10072346	Not Issued	95	02/06/2002	ADDRESS WRAP FUNCTION FOR ADDRESSABLE MEMORY DEVICES	SHEN, WILLIAM WU
10460791	6674684	150	06/11/2003	MULTI-BANK CHIP COMPATIBLE WITH A CONTROLLER DESIGNED FOR A LESSER NUMBER OF BANKS AND METHOD OF OPERATING	SHEN, WILLIAM WU
07686721	<u>5274646</u>	250		EXCESSIVE ERROR CORRECTION CONTROL	SHEN, WILLIAM WU
08570447	5761221	150		MEMORY IMPLEMENTED ERROR DETECTION AND CORRECTION CODE USING MEMORY MODULES	SHEN, WILLIAM WU
08824098	5751745	150		MEMORY IMPLEMENTED ERROR DETECTION AND CORRECTION CODE WITH ADDRESS PARITY BITS	SHEN, WILLIAM WU
09059114	6052772	150		MEMORY REQUEST PROTOCOL METHOD	SHEN, WILLIAM WU

09059221	6182174	150	II I	MEMORY CARD INTERFACE METHOD	SHEN, WILLIAM WU
09070389	6163857	150	II I	COMPUTER SYSTEM UE RECOVERY LOGIC	SHEN, WILLIAM WU
09419594	Not Issued	164	10/18/1999	ADDRESS WRAP FUNCTION FOR ADDRESSABLE MEMORY DEVICES	SHEN, WILLIAM WU
09450548	6460157	150	11/30/1999	METHOD SYSTEM AND PROGRAM PRODUCTS FOR ERROR CORRECTION CODE CONVERSION	SHEN, WILLIAM WU
09451133	6463563	150	11/30/1999	SINGLE SYMBOL CORRECTION DOUBLE SYMBOL DETECTION CODE EMPLOYING A MODULAR H- MATRIX	SHEN, WILLIAM WU
09451261	6457154	150	11	DETECTING ADDRESS FAULTS IN AN ECC-PROTECTED MEMORY	SHEN, WILLIAM WU
<u>09452079</u>	6519736	150		GENERATING SPECIAL UNCORRECTABLE ERROR CODES FOR FAILURE ISOLATION	SHEN, WILLIAM WU
10457274	Not Issued	95	11	LAYING HEAD FOR ROD ROLLING MILL	SHEN, WILLIAM X.
60389786	Not Issued	150	06/19/2002	Laying head for rod rolling mill	SHEN, WILLIAM X.
06370268	Not Issued	161		APPARATUS FOR REGULATING ADMINISTRATION OF GAS TO A SUBJECT	SHENE, WILLIAM
06606981	<u>4595019</u>	150	05/04/1984	STONE DISINTEGRATOR	SHENE, WILLIAM R.
06666770	4620545	150		NON-INVASIVE DESTRUCTION OF KIDNEY STONES	SHENE, WILLIAM R.
06772039	4606331	150	1)	ELECTRODE FOR FIBER OPTIC SCOPES	SHENE, WILLIAM R.
<u>06847696</u>	4696299	150	11	NON-INVASIVE DESTRUCTION OF KIDNEY STONES	SHENE, WILLIAM R.
06852835	4763652	150		AIMING SYSTEM FOR KIDNEY STONE DISINTEGRATOR	SHENE, WILLIAM R.
<u>07001690</u>	4737380	150		ELECTRODE WITH STRETCHED HEAT-SHRINKABLE OUTER INSULATOR	SHENE, WILLIAM R.
07342809	4938210	150	04/25/1989	INHALATION CHAMBER IN VENTILATOR CIRCUIT	SHENE, WILLIAM R.
08153091	Not Issued	166	11/17/1993	PEAK FLOW METER	SHENE, WILLIAM R.

Search and Display More Records.

Search Another: Inventor	Last Name	First Name	
Search Another. Inventor	SHEN	WILLIAM	Search

To go back use Back button on your browser toolbar.

Back to PALM ASSIGNMENT OASIS Home page



PALM INTRANET

Day: Monday Date: 2/20/2006 Time: 11:21:41

Inventor Name Search Result

Your Search was:

Last Name = SHEN

First Name = WILLIAM

Application#	Patent#	Status	Date Filed	Title	Inventor Name
08344530	<u>5627324</u>	150	11/23/1994	PEAK FLOW METER	SHENE, WILLIAM R.
<u>08438156</u>	5565630	150	05/11/1995	PEAK FLOW METER	SHENE, WILLIAM R.
07664048	Not Issued	89		MODIFIED FUEL PROCESS LOADING SYSTEM	SHENEFELT, WILLIAM B.
07164855	<u>4931656</u>	150	03/07/1988	MEANS TO DYNAMICALLY DISCHARGE A CAPACITIVELY CHARGED ELECTRICAL DEVICE	SHENG, WILLIAM
<u>07166433</u>	Not Issued	161	03/10/1988	TEMPERATURE LIMITING MEANS	SHENG, WILLIAM
<u>07316485</u>	4912335	150	02/28/1989	MEANS FOR RAPID CHARGING AND DYNAMIC DISCHARGING OF A CAPACITIVELY CHARGED ELECTRICAL DEVICE	SHENG, WILLIAM
10768725	Not Issued	71	01/30/2004	Packaged power semiconductor device having a silicon nitride ceramic substrate with active brazed copper metallization	SHENG, WILLIAM
10771204	Not Issued	95		SILICON NITRIDE INSULATING SUBSTRATE FOR POWER SEMICONDUCTOR MODULE	SHENG, WILLIAM W.
60443786	Not Issued	159		Silicon nitride ceramic substrate with active brazed copper metallization for power semiconductor "TO" packages	SHENG, WILLIAM W.
60443787	Not Issued	159		Silicon nitride ceramic substrate with integrated heat sink for power semiconductors	SHENG, WILLIAM W.
60607862	Not Issued	159		Solder-bumped power semiconductor module	SHENG, WILLIAM W.
06531310	D279182	150		FRONT PANEL FOR A GRAPHIC EQUALIZER OR SIMILAR ARTICLE	SHENK, WILLIAM B.
06373062	4535404			METHOD AND APPARATUS FOR ADDRESSING A PERIPHERAL INTERFACE BY MAPPING INTO MEMORY ADDRESS SPACE	SHENK, WILLIAM H.
06381999	4513392	150	05/25/1982	METHOD AND APPARATUS FOR	SHENK, WILLIAM H.

			GENERATING A REPETITIVE SERIAL PATTERN USING A RECIRCULATING SHIFT REGISTER	
06382000	4509118	150	METHOD AND APPARATUS FOR DEFINING MAGNETIC DISK TRACK FIELD LENGTHS USING A PROGRAMMABLE COUNTER	SHENK, WILLIAM H.

Inventor Search Completed: No Records to Display.

Search Another: Invento	Last Name	First Name	
Search Another. Inventor	SHEN	WILLIAM	Search

To go back use Back button on your browser toolbar.

Back to PALM | ASSIGNMENT | OASIS | Home page

PALM Intranet				l o
Application Number		SEARCH		
IDS Flag Clear	rance for App	lication 10614642		
IDS Information	•			
	Content	Mailroom Date Entry Number IDS Review	Reviewer	
		UPDATE		

PLUS Search Results for S/N 10614642, Searched

The Patent Linguistics Utility System (PLUS) is a USPTO automated search system for U.S. Patents from 1971 to the present. PLUS is a query-by-example search system which produces a list of patents that are most closely related linguistically to the application searched. This search was prepared by the staff of the Scientific and Technical Information Center, SIRA.